
 $^{116}\text{Sn}(\text{p,d})$ IAR [1977Se01](#)

<u>Type</u>	<u>Author</u>	<u>History Citation</u>	<u>Literature Cutoff Date</u>
Full Evaluation	Jean Blachot	NDS 113, 2391 (2012)	1-Sep-2012

E=52 MeV.

Others: $^{116}\text{Sn}({}^3\text{He},\alpha)$ E=81 MeV ([1977Se01](#)), E=110 MeV ([1978Ta22](#)).

Structure of deeply bound hole states ($1g_{9/2}, 2p_{1/2}, 2p_{3/2}$) in the region 4 to 9 MeV are analyzed for L values and spectroscopic factors; see [1977Se01](#), [1977Va15](#), [1978Ko05](#), [1978Ta22](#).

Coulomb displacement energy=13.55 MeV 5 exp, 13.57 MeV calc ([1977Se01](#)).

 ^{115}Sn Levels

<u>E(level)</u>	<u>L[†]</u>	<u>C²S</u>	<u>Comments</u>
13250	4	0.46	Analogy of ^{115}In $9/2^+$ g.s..
13730	1	0.14	Analogy of ^{115}In $1/2^-$ 336-keV state.
13980	1	0.15	Analogy of ^{115}In $3/2^-$ 597-keV state.

[†] Deduced from angular distributions compared with DWBA calc.